



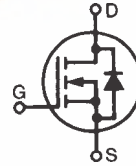
HiPerFET™ Power MOSFET

IXFN38N100Q2

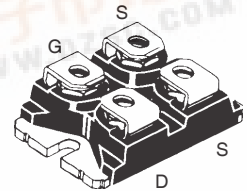
$V_{DSS} = 1000\text{ V}$
 $I_{D25} = 38\text{ A}$
 $R_{DS(on)} = 0.25\ \Omega$
 $t_{rr} \leq 300\text{ ns}$

N-Channel Enhancement Mode
 Avalanche Rated, Low Q_g , Low Intrinsic R_g
 High dV/dt , Low t_{rr}

Preliminary Data Sheet



miniBLOC, SOT-227 B (IXFN)
 E153432



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	1000	V
V_{GS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	38	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	152	A
I_{AR}	$T_C = 25^\circ\text{C}$	38	A
E_{AR}	$T_C = 25^\circ\text{C}$	60	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	5.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_g = 2\ \Omega$	20	V/ns
P_D	$T_C = 25^\circ\text{C}$	890	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS, $t = 1\text{ minute}$	2500	V
M_d	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque	1.5/13	Nm/lb.in.
Weight		30	g

G = Gate D = Drain
 S = Source

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- Double metal process for low gate resistance
- miniBLOC, with Aluminium nitride isolation
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies
- DC choppers
- Pulse generators

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8\text{ mA}$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 30\text{ V}$, $V_{DS} = 0$			$\pm 200\text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0\text{ V}$			50 mA 3 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Note 1			0.25 Ω

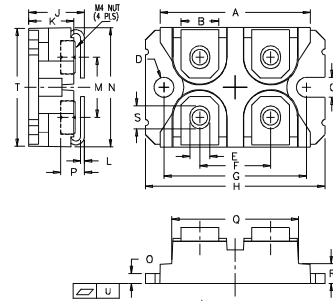


Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	V _{DS} = 20 V; I _D = 0.5 • I _{D25} Note 1	24	40	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		7200	pF
C_{oss}			950	pF
C_{rss}			170	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 1 Ω (External)		25	ns
t_r			28	ns
t_{d(off)}			57	ns
t_f			15	ns
Q_{G(on)}	V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}		250	nC
Q_{GS}			60	nC
Q_{GD}			105	nC
R_{thJC}			0.14	K/W
R_{thCK}		0.05		K/W

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
I_S	V _{GS} = 0 V			38 A
I_{SM}	Repetitive; pulse width limited by T _{JM}			152 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Note 1			1.5 V
t_{rr}	I _F = 25A -di/dt = 100 A/μs V _R = 100 V			300 ns
Q_{RM}			1.4	μC
I_{RM}			9	A

Note: 1. Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %

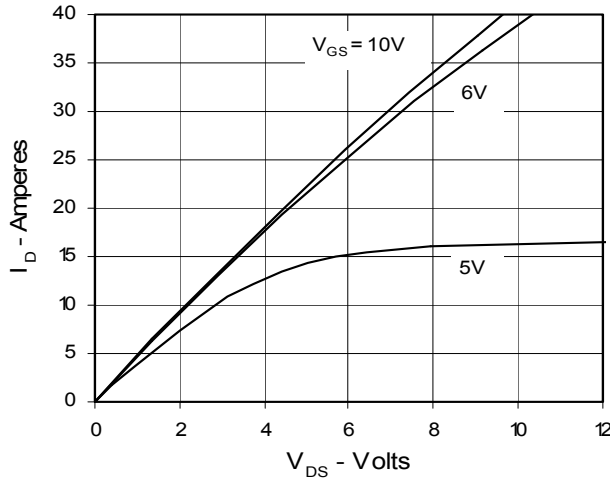
miniBLOC, SOT-227 B Outline



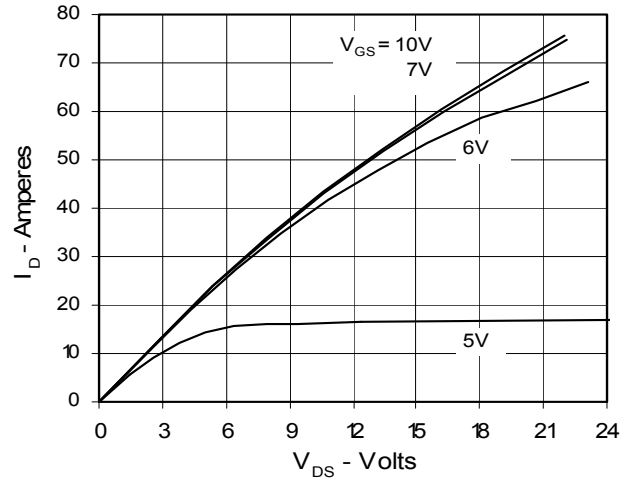
M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

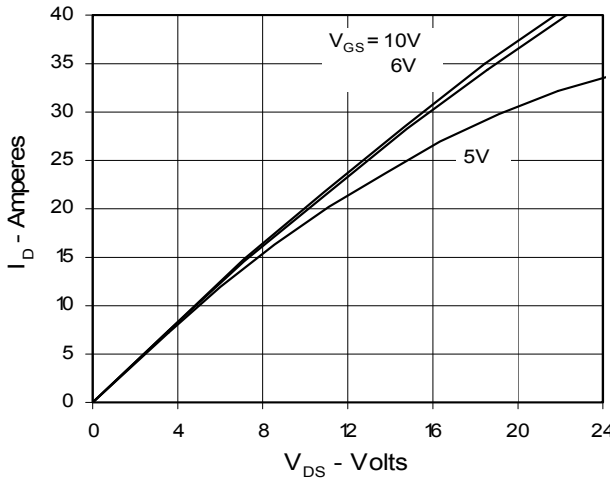
**Fig. 1. Output Characteristics
@ 25 Deg. C**



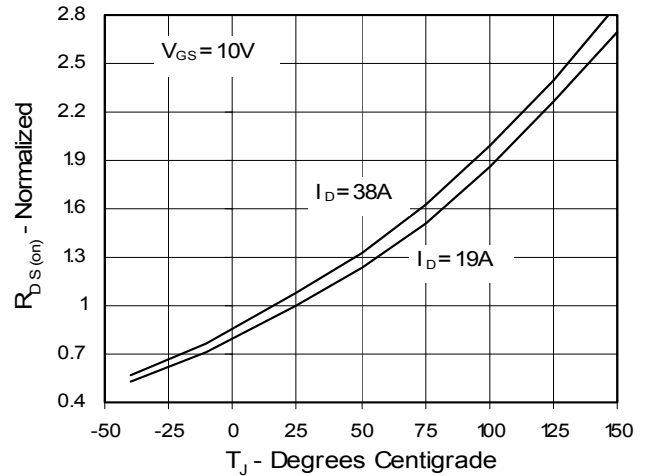
**Fig. 2. Extended Output Characteristics
@ 25 deg. C**



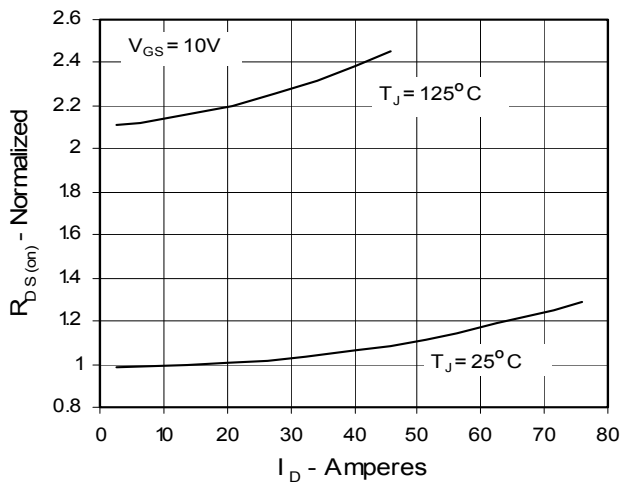
**Fig. 3. Output Characteristics
@ 125 Deg. C**



**Fig. 4. $R_{DS(on)}$ Normalized to I_{D25} Value vs.
Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to I_{D25}
Value vs. I_D**



**Fig. 6. Drain Current vs. Case
Temperature**

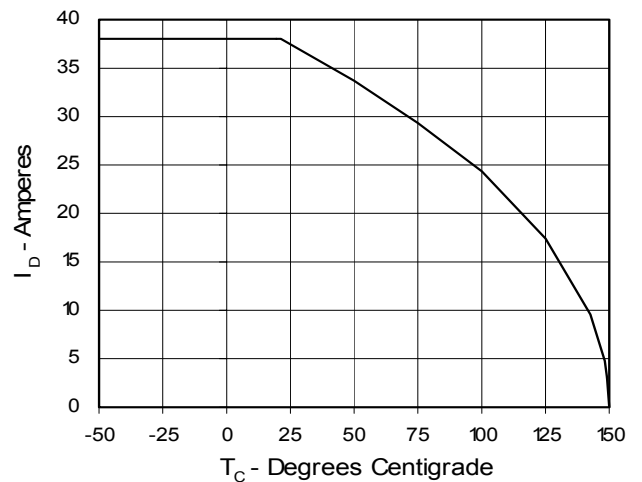


Fig. 7. Input Admittance

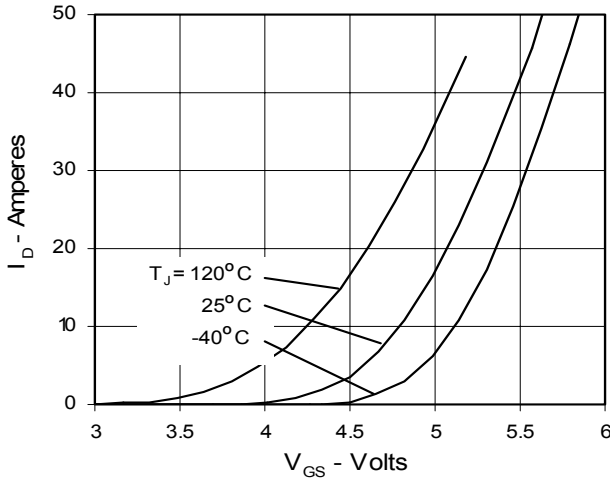


Fig. 8. Transconductance

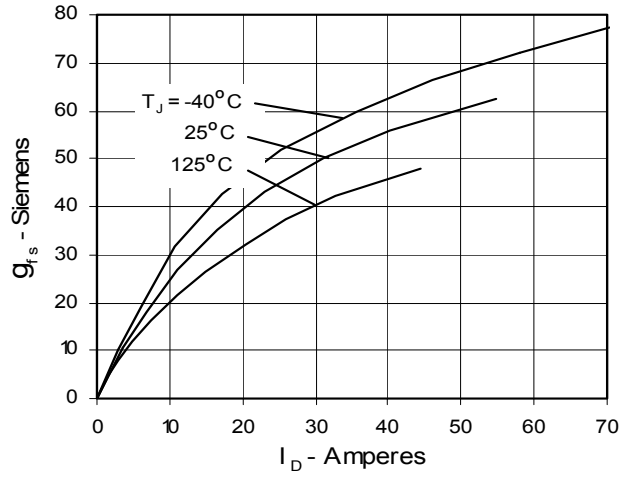


Fig. 9. Source Current vs. Source-To-Drain Voltage

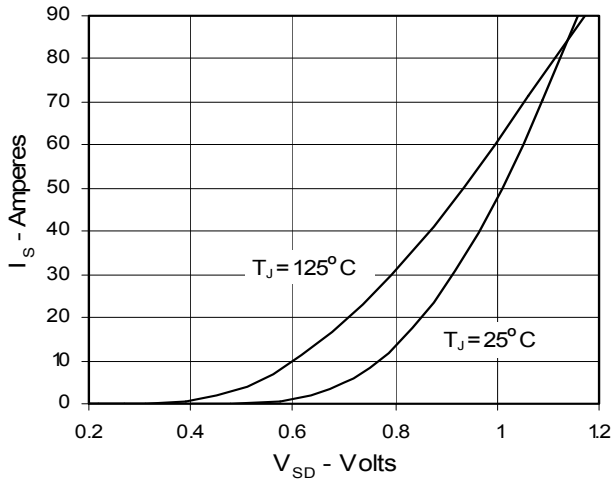


Fig. 10. Gate Charge

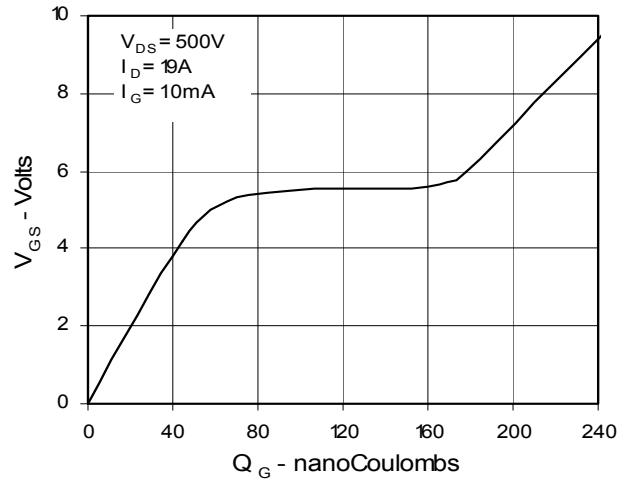


Fig. 11. Capacitance

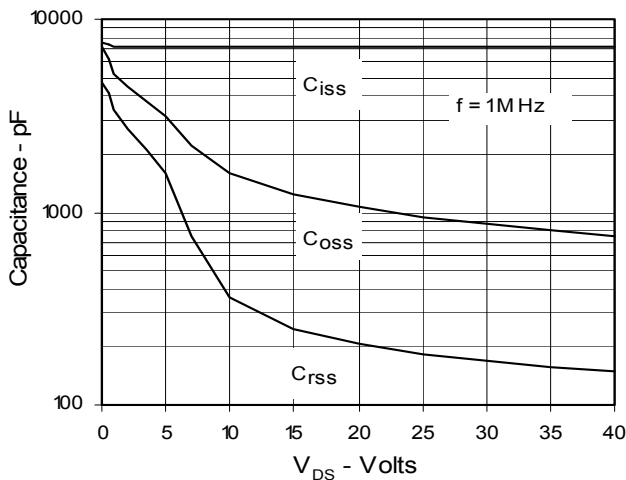


Fig. 12. Maximum Transient Thermal Resistance

